13th International Conference on Microscopy of Semiconducting Materials to be Held in Cambridge

The 13th International Conference on Microscopy of Semiconducting Materials will be held at the University of Cambridge March 31–April 3, 2003. It will focus on the latest developments in the study of the structural and electrical properties of semiconductors by the application of transmission and scanning electron microscopy (TEM and SEM), scanning probe microscopy (SPM), and x-ray-based methods. The abstract deadline is **December 2, 2002**.

The conference chairs are Tony Cullis (Sheffield University) and Paul Midgley (Cambridge University). It is sponsored by the Electron Microscopy and Analysis Group (EMAG) of the Institute of Physics, co-sponsored by The Royal Microscopical Society, and endorsed by the Materials Research Society.

Conference sessions will concentrate on key topics that include state-of-the-art studies in high-resolution imaging and analytical electron microscopy, advanced SPM and SEM applications, novel epitaxial layer phenomena, the properties of quantum nanostructures, III-nitride developments, GeSi/Si for advanced devices, metal-semiconductor contacts, and silicides and important effects of critical device-processing treatments.

Invited speakers include M. Albrecht (Erlangen University) on "Transmission Electron Microscope-Cathodoluminescence Studies of III-Nitrides"; Y. Bando (National Institute for Materials Science, Tsukuba), "Field-Emission Gun Transmission Electron Microscope Analysis of Nanotubes"; H. Bender (IMEC, Leuven), "Developments in Silicides"; D. Bimberg (Technical University, Berlin), "High-Resolution Electron Microscopy and XSTM of Quantum Dots"; G.A.D. Briggs (Oxford University), "Nanostructures for Quantum Computing"; R.M. Feenstra (Carnegie Mellon University, Pittsburgh), "SPM of GaN Surfaces"; Z. Liliental-Weber (Lawrence Berkeley Laboratory, Berkeley), "High-Resolution Electron Microscopy of Dislocations in GaN"; D.A. Muller (Lucent Technologies, Murray Hill), "Exploring the Limits of Device Physics"; V. Raineri (National Institute of Methodologies and Technologies for Microelectronics, Catania), "Process and Device Characterization"; F.M. Ross (IBM T.J. Watson Research Center, Yorktown Heights), "Ge/Si Growth on Patterned Surfaces"; and E. Zschech (AMD Saxony, Dresden), "Challenges of Failure Analysis."

The conference proceedings will be published. For further details and information on abstract submission and registration, access the conference Web site at http://physics.iop.org/IOP/Confs/MSM/ or e-mail claire.pantlin@iop.org. □

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